



# N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16409Q3

#### **FEATURES**

- Ultra Low Q<sub>g</sub> and Q<sub>gd</sub>
- Low Thermal Resistance
- Avalanche Rated
- · Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3mm x 3.3mm Plastic Package

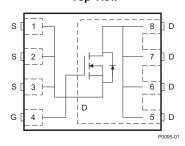
### **APPLICATIONS**

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

#### **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





#### R<sub>DS(ON)</sub> vs V<sub>GS</sub> 20 $R_{DS(on)}$ – On-State Resistance – $m\Omega$ $I_{D} = 17A$ 18 16 14 T<sub>C</sub> = 125°C 12 10 8 6 4 $T_C = 25^{\circ}C$ 2 0 2 12 V<sub>GS</sub> - Gate to Source Voltage - V G006

#### PRODUCT SUMMARY

V <sub>DS</sub>	Drain to Source Voltage 25			V
$Q_g$	Gate Charge Total (4.5V)	4	nC	
$Q_{gd}$	Gate Charge Gate to Drain	1		nC
D	Drain to Course On Registeres	V <sub>GS</sub> = 4.5V	9.5	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V	6.2	mΩ
$V_{th}$	Threshold Voltage 2		V	

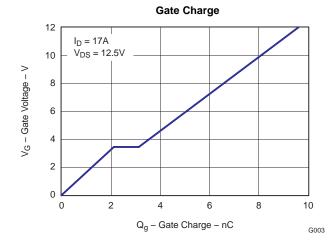
#### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship	
CSD16409Q3	SON 3.3 × 3.3 Plastic Package	13-inch reel	2500	Tape and Reel	

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	+16 / -12	V
	Continuous Drain Current, T <sub>C</sub> = 25°C	60	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	15	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	90	Α
$P_D$	Power Dissipation <sup>(1)</sup>	2.6	W
$T_J$ , $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 38A, L = 0.1 mH, R_G = 25\Omega$	72	mJ

- (1)  $R_{\theta JA} = 47^{\circ}\text{C/W}$  on  $1\text{in}^2$  Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics					
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +16/-12V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.7	2	2.3	V
	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 17A$		9.5	12.4	$m\Omega$
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_{D} = 17A$		6.2	8.2	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 17A		38		S
Dynamic	Characteristics	·				
C <sub>ISS</sub>	Input Capacitance			600	800	pF
Coss	Output Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 12.5V , f = 1MHz		480	635	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			40	55	pF
$R_g$	Series Gate Resistance			0.9	1.8	Ω
Qg	Gate Charge Total (4.5V)			4	5.6	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain	V 40.5V L 47A		1		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	V <sub>DS</sub> = 12.5V, I <sub>D</sub> = 17A		2.1		nC
Qg(th)	Gate Charge at Vth			1.1		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = 12.9V, V_{GS} = 0V$		9.1		nC
t <sub>d(on)</sub>	Turn On Delay Time			6.5		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		10.6		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_D = 17A$ , $R_G = 2\Omega$		6.3		ns
t <sub>f</sub>	Fall Time			3.4		ns
Diode C	haracteristics		•			
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 17A, V <sub>GS</sub> = 0V		0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD} = 12.9V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$		13.8		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 12.9V$ , $I_F = 17A$ , $di/dt = 300A/\mu s$		17.5		ns

#### THERMAL CHARACTERISTICS

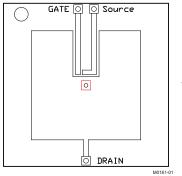
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			3.5	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient (1) (2)			59	°C/W

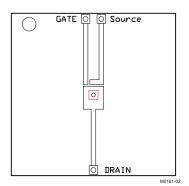
<sup>(1)</sup>  $R_{\theta JC}$  is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in 0.06 inch thick FR4 board.  $R_{\theta JC}$  is specified by design while  $R_{\theta JA}$  is determined by the user's board design.

<sup>(2)</sup> Device mounted on FR4 Material with 1 inch<sup>2</sup> of 2 oz. Cu.





Max  $R_{\theta JA} = 59^{\circ}C/W$  when mounted on 1 inch<sup>2</sup> of 2 oz. Cu.



Max  $R_{\theta JA} = 157^{\circ}C/W$  when mounted on minimum pad area of 2 oz. Cu.

## TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

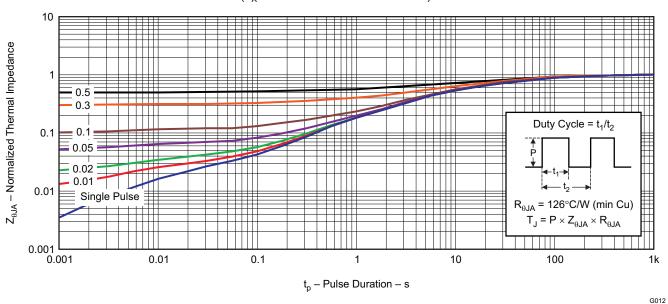


Figure 1. Transient Thermal Impedance

G012



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

## (T<sub>A</sub> = 25°C unless otherwise stated)

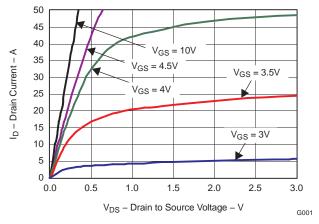


Figure 2. Saturation Characteristics

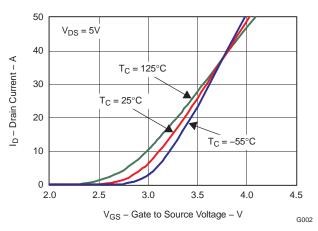


Figure 3. Transfer Characteristics

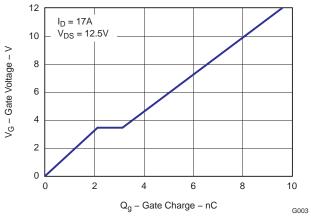


Figure 4. Gate Charge

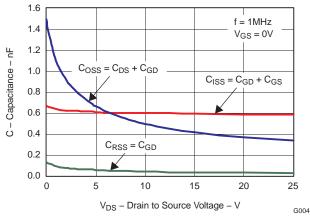


Figure 5. Capacitance

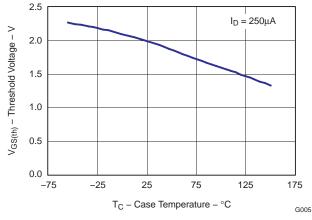


Figure 6. Threshold Voltage vs. Temperature

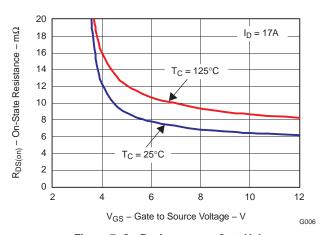


Figure 7. On Resistance vs. Gate Voltage



## TYPICAL MOSFET CHARACTERISTICS (continued)

## (T<sub>A</sub> = 25°C unless otherwise stated)

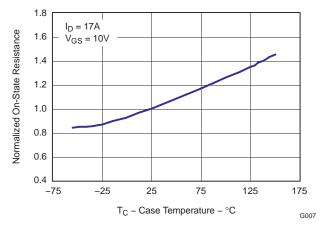


Figure 8. Normalized On Resistance vs. Temperature

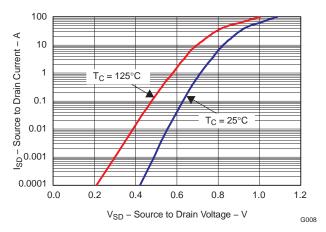


Figure 9. Typical Diode Forward Voltage

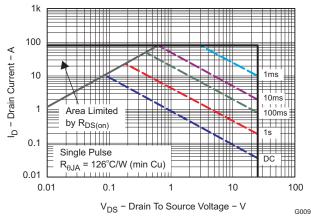


Figure 10. Maximum Safe Operating Area

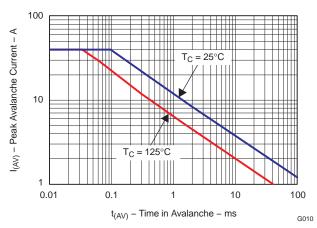


Figure 11. Single Pulse Unclamped Inductive Switching

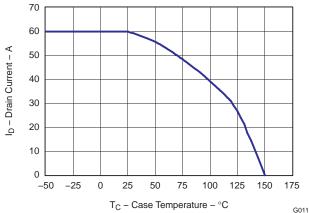
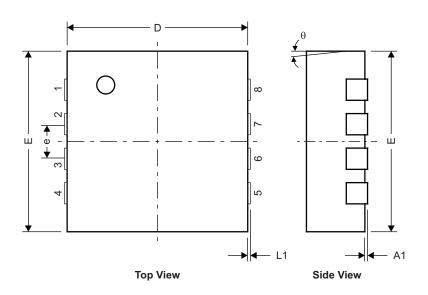


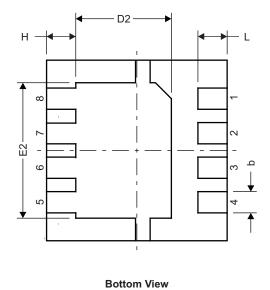
Figure 12. Maximum Drain Current vs. Temperature

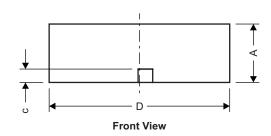


## **MECHANICAL DATA**

# **Q3 Package Dimensions**





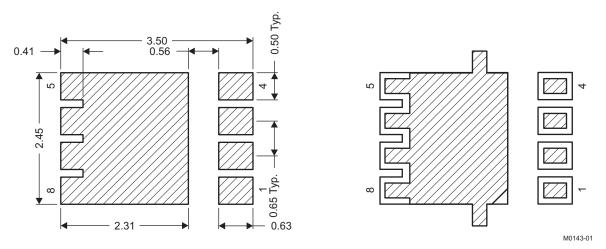


M0142-01

DIM		MILLIMETERS	}	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	_	_	_	_	_	_	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
Е	3.200	3.300	3.400	0.126	0.130	0.134	
E1	_	_	_	_	_	_	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е		0.650 TYP	P 0.026			•	
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	_	-	-	-		_	
θ	_	_	-	-	_	_	

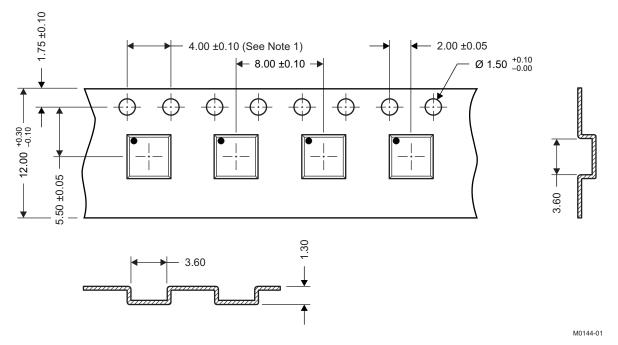


#### **Recommended PCB Land Pattern**



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Q3 Tape and Reel Information**



#### Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

## SLPS204A - AUGUST 2009-REVISED MAY 2010



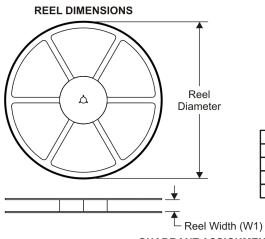
## **REVISION HISTORY**

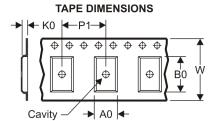
Cł	nanges from Original (August 2009) to Revision A	Pag	e
•	Deleted the Package Marking Information section		7

# PACKAGE MATERIALS INFORMATION

www.ti.com 23-May-2011

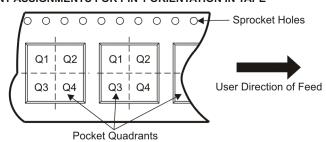
## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16409Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

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#### \*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
I	CSD16409Q3	SON	DQG	8	2500	335.0	335.0	32.0

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